



Low-Voltage Single SPDT Analog Switch

DESCRIPTION

The DG9431 is a single-pole/double-throw monolithic CMOS analog device designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 35 ns, t_{OFF} : 20 ns), low on-resistance ($r_{DS(on)}$: 20 Ω) and small physical size (TSOP-6), the DG9431 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9431 is built on Vishay Siliconix's low voltage BCD-15 process. Minimum ESD protection, per Method 3015.7, is 2000 V. An epitaxial layer prevents latchup. Break-before -make is guaranteed for DG9431.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For analog switching products manufactured with 100 % matte tin device terminations, the lead (Pb)-free "-E3" suffix is being used as a designator.

FEATURES

- Low Voltage Operation (+ 2.7 to + 5 V)
- Low On-Resistance r_{DS(on)}: 20 Ω
- Fast Switching t_{ON}: 35 ns, t_{OFF}: 20 ns
- Low Leakage I_{COM(on)}: 200-pA max
- Low Charge Injection Q_{INJ}: 1 pC
- Low Power Consumption
- TTL/CMOS Compatible
- ESD Protection > 2000 V (Method 3015.7)
- Available in TSOP-6 and SOIC-8
- · Lead (Pb)-Free Version is RoHS Compliant

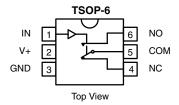
BENEFITS

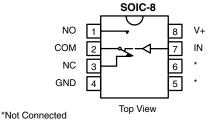
- · Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- · Reduce Board Space (TSOP-6)

APPLICATIONS

- · Battery Operated Systems
- Portable Test Equipment
- · Sample and Hold Circuits
- · Cellular Phones
- Communication Systems
- · Military Radio
- PBX, PABX Guidance and Control Systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRUTH TABLE				
Logic	NC	NO		
0	ON	OFF		
1	OFF	ON		

Logic "0" \leq 0.8 V Logic "1" \geq 2.4 V

ORDERING INFORMATION				
Temp Range	Package	Part Number		
- 40 to 85 °C	TSOP-6	DG9431DV-T1 DG9431DV-T1-E3 (Lead (Pb)-free)		
	SOIC-8	DG9431DY-T1 DG9431DY-T1-E3 (Lead (Pb)-free)		

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

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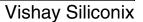


ABSOLUTE MAXIMUM RATINGS					
Parameter		Limit	Unit		
Reference V+ to GND		- 0.3 to + 13	V		
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	7 v		
Continuous Current (Any Terminal)		± 20	mA		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 40			
ESD (Method 3015.7)		> 2000	V		
Storage Temperature (D Suffix)		- 65 to 125	°C		
Power Dissipation (Packages) ^b	8-Pin Narrow Body SOIC ^c	400	mW		

Notes:

- a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board. c. Derate 6.5 mW/°C above 75 °C.

SPECIFICATIONS (V-	+ = 3 V)						
	-	Test Conditions Unless Otherwise Specified		D Suffix - 40 to 85 °C			
Parameter	Symbol	$V+ = 3 V$, $\pm 10 \%$, $V_{IN} = 0.8 \text{ or } 2.4 V^e$	Temp ^a	Min ^c	Typ ^b	Max ^c	Unit
Analog Switch							
Analog Signal Range ^d	V_{ANALOG}		Full	0		3	V
Drain-Source On-Resistance	r _{DS(on)}	V_{NO} or $V_{NC} = 1.5 \text{ V}, V_{+} = 2.7 \text{ V}$ $I_{COM} = 5 \text{ mA}$	Room Full		30	50 80	
r _{DS(on)} Match ^d	$\Delta r_{DS(on)}$	V_{NO} or $V_{NC} = 1.5 \text{ V}$	Room		0.4	2	Ω
r _{DS(on)} Flatness ^f	r _{DS(on)} Flatness	V_{NO} or $V_{NC} = 1$ and 2 V	Room		4	8	
NO or NC Off Leakage Current ^g	I _{NO/NC(off)}	V_{NO} or V_{NC} = 1 V/2 V, V_{COM} = 2 V/1 V	Room Full	- 100 - 5000	5	100 5000	pA
COM Off Leakage Current ^g	I _{COM(off)}	$V_{COM} = 1 \text{ V/2 V}, V_{NO} \text{ or } V_{NC} = 2 \text{ V/1 V}$	Room Full	- 100 - 5000	5	100 5000	
Channel-On Leakage Current ^g	I _{COM(on)}	$V_{COM} = V_{NO}$ or $V_{NC} = 1 \text{ V/2 V}$	Room Full	- 200 - 10000	10	200 10000	
Digital Control							
Input Current	I _{INL} or I _{INH}		Full		1		μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}		Room Full		50	120 200	
Turn-Off Time	t _{OFF}	V_{NO} or $V_{NC} = 1.5 \text{ V}$	Room Full		20	50 120	ns
Break-Before-Make Time	t _d		Room	3	20		
Charge Injection	Q_{INJ}	$C_L = 1 \text{ nF, } V_{gen} = 0 \text{ V, } R_{gen} = 0 \Omega$	Room		1	5	рС
Off-Isolation	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 74		dB
Source Off Capacitance	C _{S(off)}	f = 1 MHz	Room		7		pF
Channel-On Capacitance	C _{D(on)}	I = I IVIDZ	Room		32		ρι
Power Supply			•			•	
Power Supply Range	V+			2.7		12	V
Power Supply Current	l+	$V+ = 3.3 \text{ V}, V_{IN} = 0 \text{ or } 3.3 \text{ V}$				1	μΑ





SPECIFICATIONS (V-	+ = 5 V)						
	Test Conditions Unless Otherwise Specified			D Suffix - 40 to 85 °C			
Parameter	Symbol	$V+ = 5 V$, $\pm 10 \%$, $V_{IN} = 0.8 \text{ or } 2.4 V^e$	Temp ^a	Min ^c	Typ ^b	Max ^c	Unit
Analog Switch						•	
Analog Signal Range ^d	V _{ANALOG}		Full	0		5	V
Drain-Source On-Resistance	r _{DS(on)}	V_{NO} or $V_{NC} = 3.5 \text{ V}$, $V_{+} = 4.5 \text{ V}$ $I_{COM} = 5 \text{ mA}$	Room Full		20	30 50	
r _{DS(on)} Match ^d	$\Delta r_{DS(on)}$	V _{NO} or V _{NC} = 1.5 V	Room		0.4	2	Ω
r _{DS(on)} Flatness ^f	r _{DS(on)} Flatness	V_{NO} or V_{NC} = 1, 2 and 3 V	Room		2	6	
NO or NC Off Leakage Current	I _{NO/NC(off)}	V_{NO} or V_{NC} = 1 V/4 V, V_{COM} = 4 V/1 V	Room Full	- 100 - 5000	10	100 5000	
COM Off Leakage Current	I _{COM(off)}	$V_{COM} = 1 \text{ V/4 V}, V_{NO} \text{ or } V_{NC} = 4 \text{ V/1 V}$	Room Full	- 100 - 5000	10	100 5000	pА
Channel-On Leakage Current	I _{COM(on)}	$V_{COM} = V_{NO}$ or $V_{NC} = 1 \text{ V/4 V}$	Room Full	- 200 - 10000		200 10000	
Digital Control							
Input Current	I _{INL} or I _{INH}		Full		1		μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}		Room Full		35	75 150	
Turn-Off Time	t _{OFF}	V_{NO} or $V_{NC} = 3.0 \text{ V}$	Room Full		20	50 100	ns
Break-Before-Make Time	t _d		Room	3	10		
Charge Injection	Q _{INJ}	$C_L = 1 \text{ nF, } V_{gen} = 0 \text{ V, } R_{gen} = 0 \Omega$	Room		2	5	рC
Off-Isolation	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 74		dB
NC and NO Capacitance	C _(off)	f = 1 MHz	Room		- 7		pF
Channel-On Capacitance	C _{D(on)}	I = I MHZ	Room		32		ρι
Power Supply			•				
Power Supply Range	V+			2.7		12	V
Power Supply Current	I+	$V+ = 5.5 \text{ V}, V_{IN} = 0 \text{ or } 5.5 \text{ V}$				1	μΑ

Notes

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.
- g. Guraranteed by 5-V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

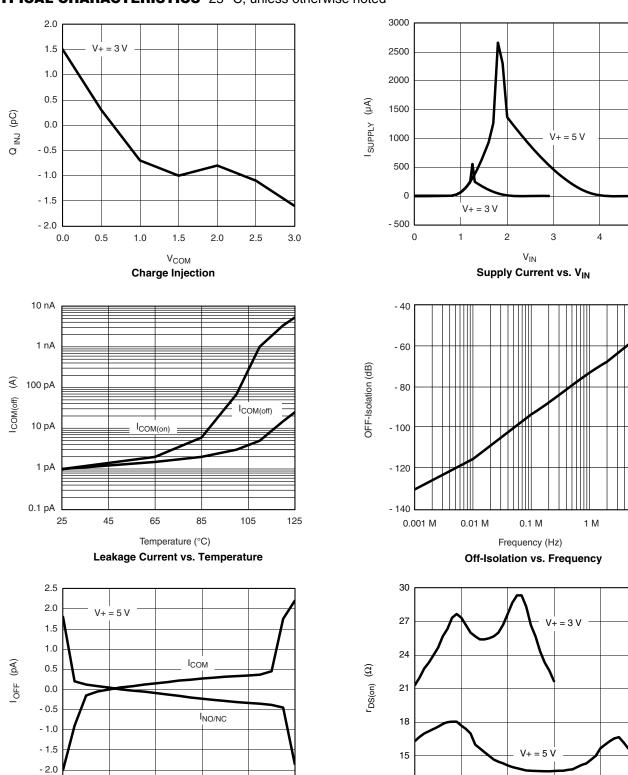
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



12

0

1

2

3

 V_{COM}

r_{DS} vs. V_{COM}

- 2.5

0

2

 $$V_{\text{COM}}$$ Off-Leakage vs. Voltage at 25 $^{\circ}\text{C}$

3

4

4

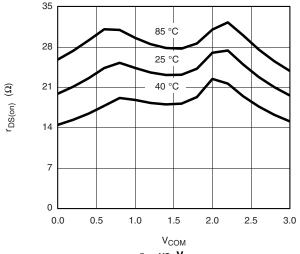
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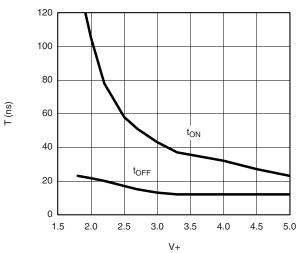




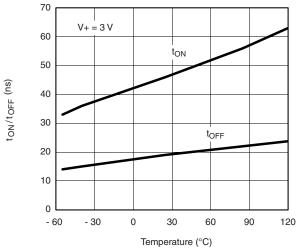
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



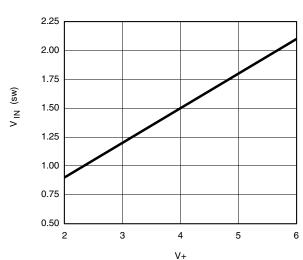




 $t_{\rm ON}/t_{\rm OFF}$ vs. Power Supply Voltage



Switching Time vs. Temperature

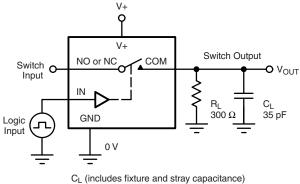


Input Switching Point vs. Power Supply Voltage

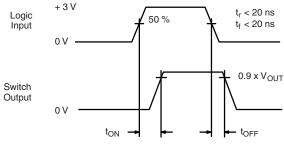
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TEST CIRCUITS



$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

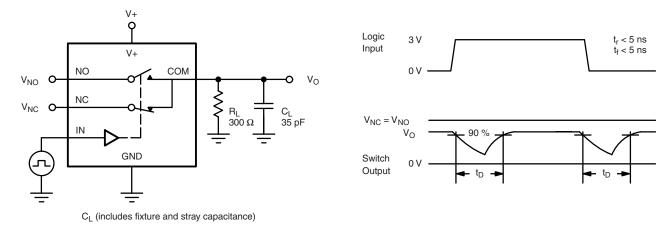


Figure 2. Break-Before-Make Interval

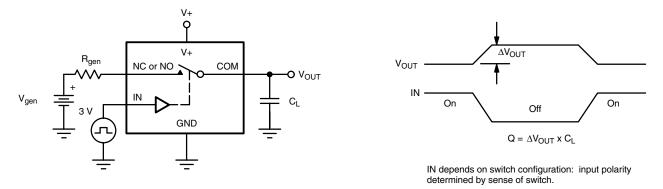


Figure 3. Charge Injection



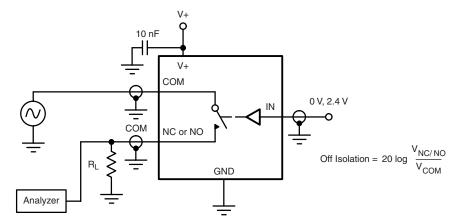


Figure 4. Off-Isolation

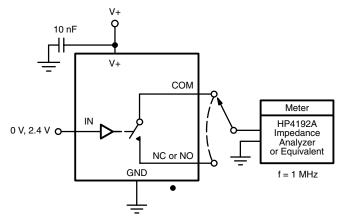


Figure 5. Channel Off/On Capacitance

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